















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	EV2SC4793-T5
Overseas Part Number	2SC4793
▶ Equivalent Part Number	2SC4793

"T5" means TO-220F



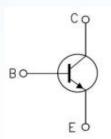


Silicon PNP transistor

Power Amplifier Applications

- ① Complementary to 2SA1837
- ② High collector voltage:VCEO=230V (min)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the Absolute maximum ratings.





TO-220F

Absolute Maximum °C):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	230	V
Collector-emitter voltage	V _{CEO}	230	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	Ic	1	Α
Base current	I _B	0.2	Α
Collector power dissipation (Tc=25°C)	P _C	50	W
Junction temperature	Tj	150	$^{\circ}$ C
Storage temperature range	T _{STG}	-55~150	°C

Thermal Characteristics

Symbol	Paramter	Тур	Units
R _{OJC}	Junction-to-Case	3.0	°C/W



Silicon PNP transistor

Electrical Characteristics $^{\circ}$ C):

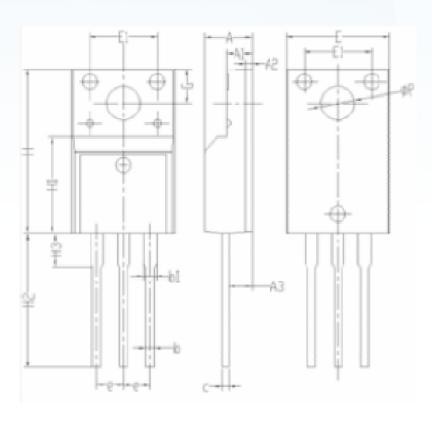
Characteristics	Symbol	Test Condition	Min	Тур	Max	Unit
Collector-Base Cut-off Current	I _{CBO}	V _{CB} =230V,I _E =0			1.0	uA
Emitter-Base Cut-off Current	I _{EBO}	V _{EB} =5V,I _C =0			1.0	uA
Collector-Emitter Breakdown Voltage	V_{CEO}	I _C =1mA	230			V
DC current gain	h _{FE}	I _C =0.1A; V _{CE} =5V	100		300	
Collector-emitter saturation voltage	V _{CEsat}	I _C =0.5A; I _B =0.05A			0.5	V
Base-Emitter Saturation Voltage	V _{BEsat}	I _C =0.5A,I _B =0.05A			1.4	V
Base-emitter voltage	V _{BE}	V _{CE} =5V;I _C =0.5A			1.5	V
Transition frequency	f _T	V _{CE} =10V;I _C =100mA		40		MHz



Silicon PNP transistor

Package Information

TO-220F PACKAGE



Symbol	Dimensions (millimeters)		
	Min	Max	
А	4.35	4.75	
A1	2.30	2.70	
A2	0.40	0.80	
A3	2.1	2.50	
b	0.60	1.00	
b1	1.00	1.40	
С	0.30	0.70	
e	2.30	2.70	
E	9.80	10.2	
E1	6.30	6.70	
Н	15.6	16.0	
H1	8.80	9.20	
H2	12.9	13.5	
H3	3.10	3.50	
G	3.10	3.50	
фР	3.10	3.50	



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